Supporting information

Role of Anatase/TiO₂(B) heterointerface for ultrastable high-rate lithium and sodium energy storage performance

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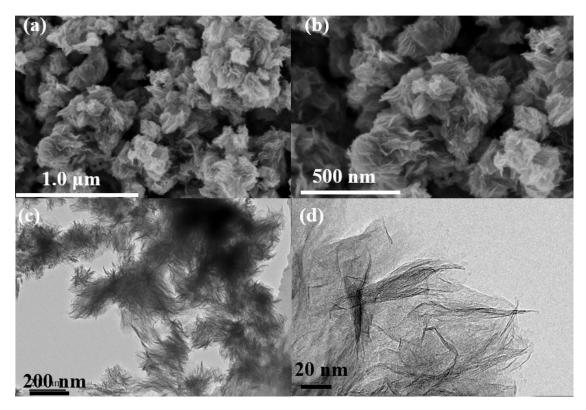


Fig. S1 (a, b) SEM and (c, d) TEM images of TAB/C precursor.

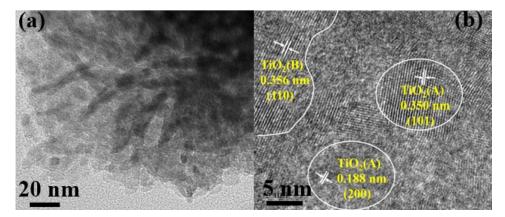


Fig. S2 HRTEM images of TAB.

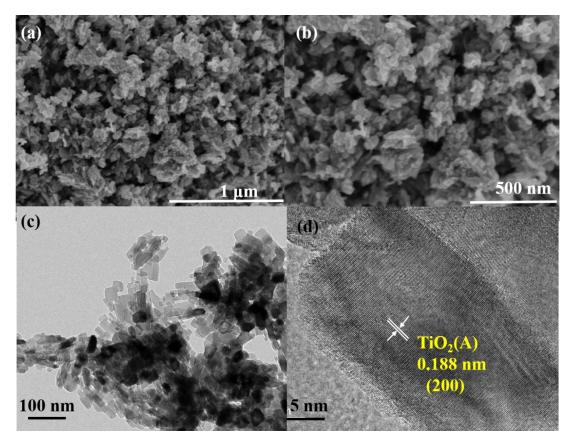


Fig. S3 (a, b) SEM and (c, d) TEM images of TA nanoparticles.

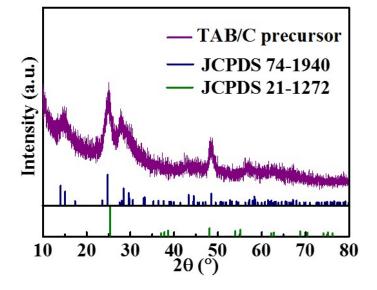


Fig. S4 XRD pattern of TAB/C precursor.

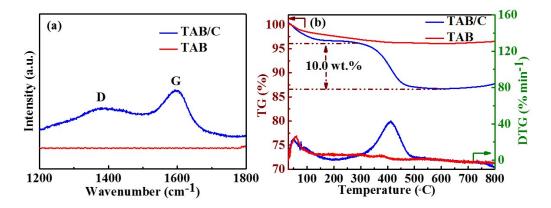


Fig. S5 (a) Raman spectra and (b) TGA curves of TAB/C and TAB.

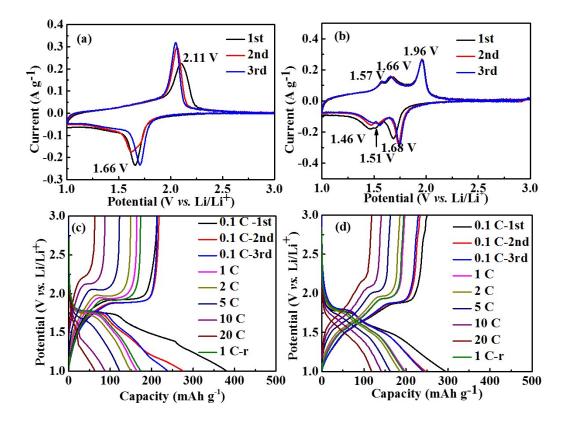


Fig. S6 CV curves at 0.1 mV s⁻¹ of (a) TA and (b) TAB for LIBs; galvanostatic charge/discharge (GCD) curves of (c) TA and (d) TAB for LIBs, where the label 1 C-r represents the result when the current density reverts from 20 C to 1 C.

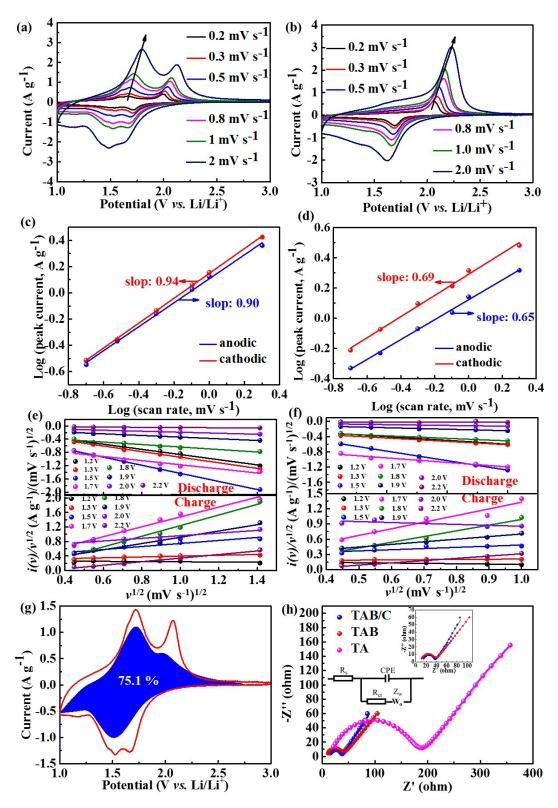


Fig. S7 Kinetics analysis for LIBs: CV curves at different scan rates of (a) TAB and (b) TA; log(i)-log(v) plots of CV curves to determine *b*-values of (c) TAB and (d) TA; $i(v)/v^{1/2}$ vs. $v^{1/2}$ at different potentials during charge/discharge cycles of (e) TAB/C and (f) TAB; (g) capacitive contribution (blue region) of TAB at 0.8 mV s⁻¹; (h) EIS

spectra of the TAB/C, TAB and TA electrodes after 1000 cycles at 10 C, inserts are the equivalent circuit model and the enlarged view of EIS.

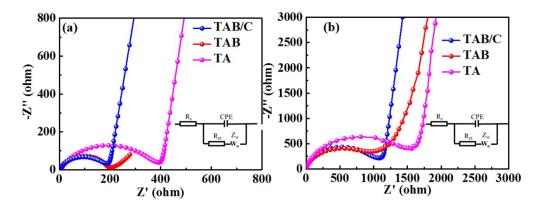


Fig. S8 EIS spectra of the TAB/C, TAB and TA electrodes in (a) LIBs and (b) SIBs before cycles, inserts are the equivalent circuit models.

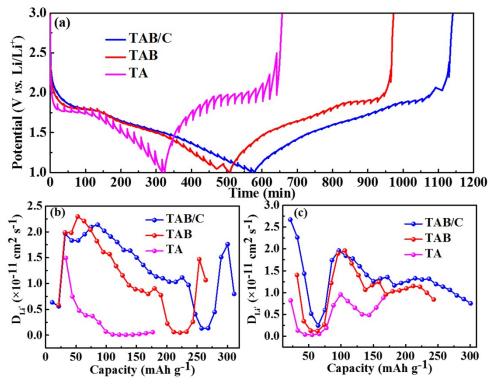


Fig. S9 (a) GITT profiles for LIBs; D_{Li^+} as a function of (b) discharge capacity and (c) charge capacity for LIBs.

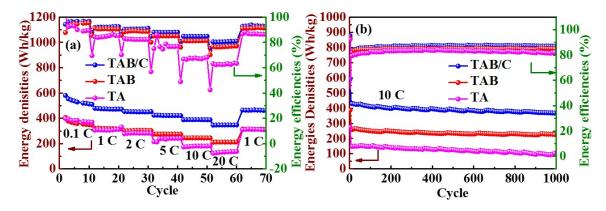


Fig. S10 Energy densities and energy efficiencies of the TAB/C, TAB and TA electrodes for LIBs during rate (a) and cycle (b) tests.

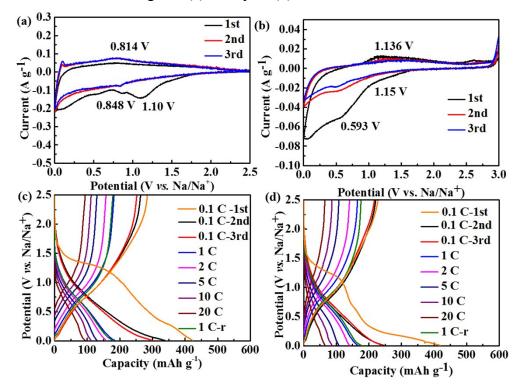


Fig. S11 CV curves at 0.1 mV s⁻¹ of (a) TAB and (b) TA for SIBs; GCD curves of (c) TAB and (d) TA for SIBs, where the label 1 C-r represents the result when the current density reverts from 20C to 1 C.

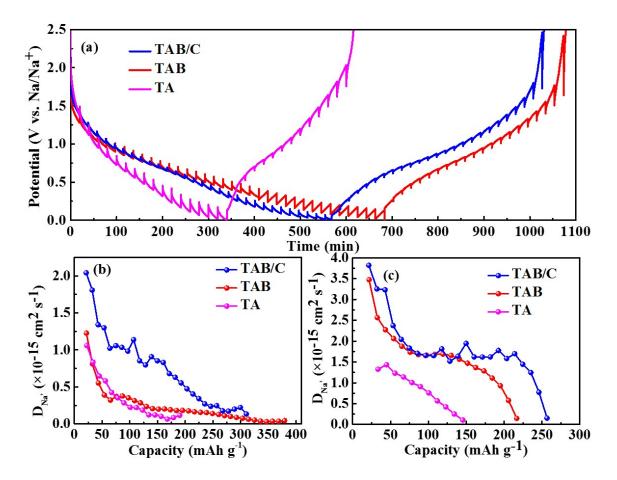


Fig. S12 (a) GITT profiles for SIBs; D_{Na^+} as a function of (b) discharge capacity and (c) charge capacity for SIBs.

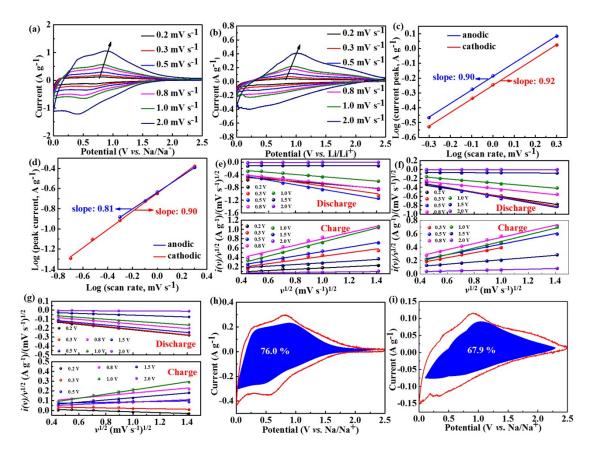


Fig. S13 Kinetics analysis of SIBs: CV curves at different scan rates of (a) TAB and (b) TA; log(i)-log(v) plots of CV curves to determine *b*-values of (c) TAB and (d) TA; $i(v)/v^{1/2}$ vs. $v^{1/2}$ at different potentials during charge/discharge cycles for (e) TAB/C, (f) TAB and (g) TA; capacitive contributions (blue region) of (h) TAB and (i) TA at 0.5 mV s⁻¹.

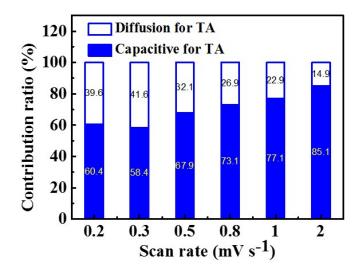


Fig. S14 Capacity contributions from diffusion-controlled and capacitive behaviors of the TA electrode at different scan rates for SIBs.

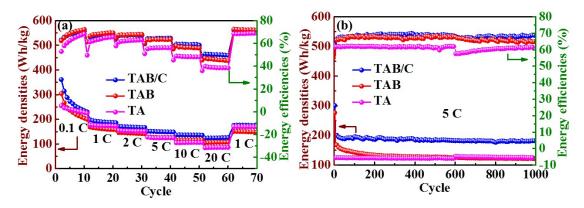


Fig. S15 Energy densities and energy efficiencies of the TAB/C, TAB and TA electrodes for SIBs during rate (a) and cycle (b) tests.

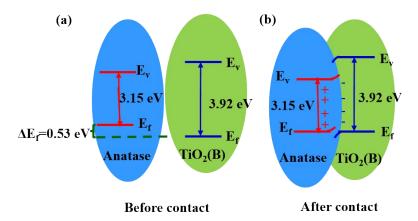


Fig. S16 Formation mechanism and direction of the internal electric field when the heterostructure is formed from the anatase and $TiO_2(B)$ phases: (a) before and (b) after formation.

Electrode materials	Surface area (m ² g ⁻¹)	Pore volume (cm ³ g ⁻¹)
TAB/C	125	0.55
TAB	95	0.45

Table S1 Surface area and pore volume of TAB/C and TAB.

Table S2 Impedance parameters of the TAB/C, TAB and TA electrodes before and after 1000 cycles for LIBs and SIBs.

Battery	Flastrado	F	resh	Electrodes after		
	Electrode	elec	trodes	cycles		
systems	materials	R _s /Ω	R_{ct}/Ω	R_s/Ω	R_{ct}/Ω	
	TAB/C	4.1	170.4	12.9	24.2	
LIBs	TAB	2.2	182.9	9.0	28.5	
	ТА	5.5	368.6	8.5	111.8	
	TAB/C	4.0	785.1	6.6	129.9	
SIBs	TAB	3.9	955.0	3.3	308.5	
	ТА	4.5	1372.0	13.2	334.5	

Materials	Battery system	Cyclic performance ^a	Rate performance ^a	Reference
ТАВ/С		212 mAh g ⁻¹ after 1000 cycles at 10 C	193 mAh g ⁻¹ at 20 C	This work
AB550		190 mAh g ⁻¹ after 1000 cycles at 10 C	150 mAh g ⁻¹ at 20 C	41
TiO ₂ (AB)-2		103 mAh g ⁻¹ after 1000 cycles at 10 C	80 mAh g ⁻¹ at 20 C	6
TAB Nanowires		-	160 mAh g ⁻¹ at 20 C	58
TAB300		210 mAh g ⁻¹ after 60 cycles at 2 C	110 mAh g ⁻¹ at 20 C	40
TiO ₂ (B)-HTs	LIBs	160 mAh g ⁻¹ after 400 cycles at 10 C	160 mAh g ⁻¹ at 20 C	35
TiO _{2-x} /CNT		~160 mAh g ⁻¹ after 1000 cycles at 6 C	155 mAh g ⁻¹ at 12 C	33
TiO ₂ /RGO		130 mAh g ⁻¹ after 1000 cycles at 10 C	152 mAh g ⁻¹ at 10 C	12
H-TiO ₂ @C ^b		126 mAh g ⁻¹ after 200 cycles at 6 C	50 mAh g ⁻¹ at 10 C	29
TiO _{2-x} /GQDs		168 mAh g ⁻¹ after 100 cycles at 10 C	155 mAh g ⁻¹ at 20 C	27
Hollow TiO ₂		195 mAh g ⁻¹ after 600 cycles at 0.6 C	196 mAh g ⁻¹ at 6 C	25
TAB/C		172 Ab	112 mAh g ⁻¹ at 20 C	
		173 mAh g ⁻¹ after 1000 cycles at 5 C	144 mAh g ⁻¹ at 10 C	This work
TAB300 ^b		80 mAh g ⁻¹ after 30 cycles at 0.2 C	-	40
TiO ₂ (B) belts ^b		211 mAh g ⁻¹ after 500 cycles at 1 C	106 mAh g ⁻¹ at 20 C	38

Table S3 Electrochemical performance of state-of-the-art TiO₂-based anode materials for LIBs and SIBs.

TiO ₂ (B) wires			150 mAh	n g ⁻¹ after 50 cycl	es at 0.12 C	82.	3 mAh g ⁻¹ at	1.2 C	S1	
TiO _{2-x} /CNT	SIE	Bs	~140 mAh g ⁻¹ after 1000 cycles at 6 C		118 mAh g ⁻¹ at 12 C			33		
TiO ₂ nanotubes			126 mA	h g ⁻¹ after 100 cy	cles at 1 C	12	9 mAh g ⁻¹ at	10 C	52	
C coupled TiO ₂			100 mAh	g ⁻¹ after 2000 cy	cles at 20 C	11	1 mAh g ⁻¹ at	20 C	20	
TiO ₂ /NC ^b			137 mAh	g ⁻¹ after 1000 cy	cles at 10 C	10	4 mAh g ⁻¹ at	20 C	23	
TiO ₂ @CNTs/CFP	b		179 mAł	n g ⁻¹ after 400 cyc	cles at 12 C	12	9 mAh g ⁻¹ at	12 C	24	
TiO ₂ @NFG			146 mAh	g ⁻¹ after 8000 cy	cles at 10 C	12	9 mAh g ⁻¹ at	20 C	3	
^a 1 C=168 mAh g ⁻¹ .										
b Data	obtained	in	the	potential	range	of	0.05	_	3.0	V

References

S1. J. Lee, J. K. Lee, K. Y. Chung, H. G. Jung, H. Kim, J. Mun and W. Choi, *Electrochim. Acta* 2016, *200*, 21-28.